**Product data sheet** 

## 1. General description

Dual Silicon Carbide Schottky diode in a TO247-3L plastic package, designed for high frequency switched-mode power supplies.



### 2. Features and benefits

- · Highly stable switching performance
- High forward surge capability I<sub>FSM</sub>
- · Extremely fast reverse recovery time
- · Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- · Reduced cooling requirements
- RoHS compliant
- High junction operating temperature capability (T<sub>i(max)</sub> = 175 °C)

## 3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage			12	200		V
Io	limiting average forward current	T <sub>mb</sub> ≤ 139 °C; DC; both diodes	40			А	
T <sub>j</sub>	junction temperature		175			°C	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 5</u>		-	1.45	1.65	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 150 °C; per diode; <u>Fig. 5</u>		-	1.95	2.30	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 5</u>		-	2.10	2.60	V
Dynamic	characteristics				'	'	
$Q_r$	recovered charge	$I_F = 20 \text{ A}$ ; $dI_F/dt = 500 \text{ A/µs}$ ; $V_R = 400 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; per diode; Fig. 7		-	44	-	nC

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	K	cathode	<b>ТОЧ</b>	A1
3	A2	anode		K
mb	mb	mounting base; connected to cathode	1 2 3	sym125

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSC2D401200CW	TO247	WNSC2D401200CW6Q	Tube	30	SOT429 (L)	25-Mar-2013
					TO247P (P)	09-Mar-2023

# 7. Marking

### **Table 4. Marking codes**

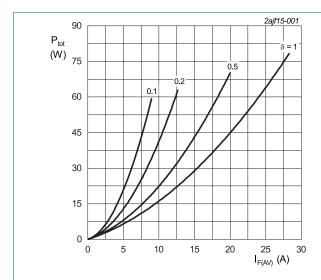
Type number	Marking codes
WNSC2D401200CW	WNSC2D 401200CW

# 8. Limiting values

### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		1200	V
$V_{\text{RWM}}$	crest working reverse voltage		1200	V
$V_R$	reverse voltage	DC	1200	V
Io	limiting average forward	T <sub>mb</sub> ≤ 139 °C; DC; both diodes	40	Α
	current	T <sub>mb</sub> ≤ 125 °C; DC; both diodes	49	Α
		T <sub>mb</sub> ≤ 25 °C; DC; both diodes	84	Α
I <sub>FRM</sub>	repetitive peak forward current	$δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 125 °C$ ; square-wave pulse; per diode	37	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	160	А
		$t_p$ = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse; per diode	1000	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	sine-wave pulse; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 10 \text{ ms}$	128	A <sup>2</sup> s
T <sub>stg</sub>	storage temperature		-55 to 175	°C
T <sub>j</sub>	junction temperature		-55 to 175	°C



$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 0.981 \text{ V; } R_s = 0.0631 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

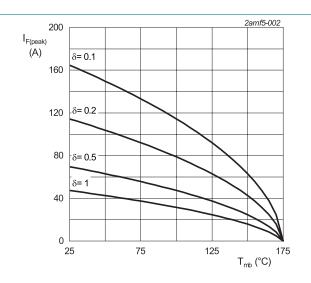
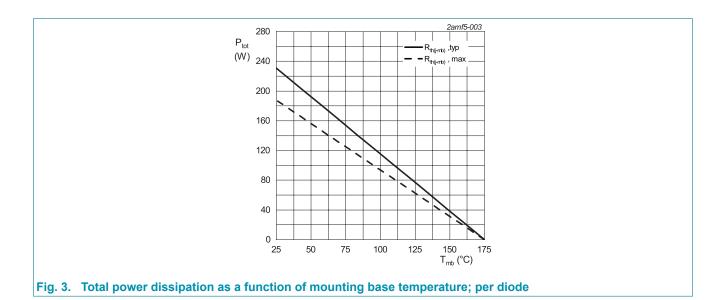


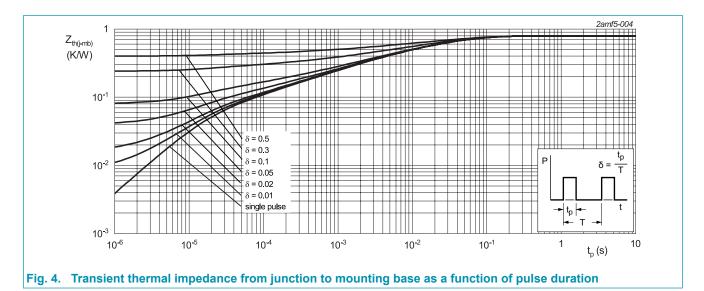
Fig. 2. Current derating as a function of mounting base temperature; per diode



## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

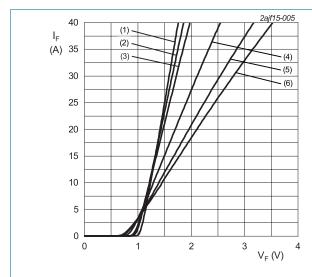
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance	per diode; Fig. 4	-	0.65	8.0	K/W
	from junction to mounting base	both diodes conducting	-	0.31	0.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	40	-	K/W



## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>F</sub>	forward current	I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 5</u>	-	1.45	1.65	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 150 °C; per diode; <u>Fig. 5</u>	-	1.95	2.30	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 5</u>	-	2.10	2.60	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 1200 V; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>	-	1	100	μA
		V <sub>R</sub> = 1200 V; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 6</u>	-	25	1000	μA
Dynamic	characteristics					
Q <sub>r</sub>	recovered charge	$I_F = 20 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 500 \text{ A/µs}$ ; $T_j = 25 ^{\circ}\text{C}$ ; per diode; Fig. 7	-	44	-	nC
C <sub>d</sub>	diode capacitance	$f = 1 \text{ MHz}$ ; $V_R = 1 \text{ V}$ ; $T_j = 25 ^{\circ}\text{C}$ ; per diode	-	927	-	pF
		$f = 1 \text{ MHz}$ ; $V_R = 400 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; per diode	-	84	-	pF
		f = 1 MHz; V <sub>R</sub> = 800 V; T <sub>j</sub> = 25 °C; per diode	-	63	-	pF
E <sub>as</sub>	non-repetitive avalanche energy	$I_R$ = 5.3 A; L = 10 mH; $T_{j(init)}$ = 25 °C; per diode	140	-	-	mJ



 $V_o$  = 0.981 V;  $R_s$  = 0.0631  $\Omega$ 

(1)  $T_j = -55$  °C; typical values

(2) T<sub>j</sub> = 0 °C; typical values

(3) T<sub>i</sub> = 25 °C; typical values

(4)  $T_j = 100 \, ^{\circ}\text{C}$ ; typical values

(5)  $T_j = 150$  °C; typical values

(6) T<sub>i</sub> = 175 °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values; per diode

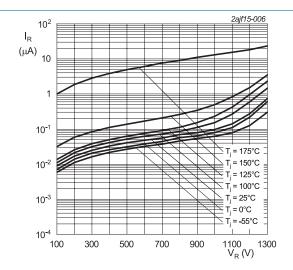


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value; per diode

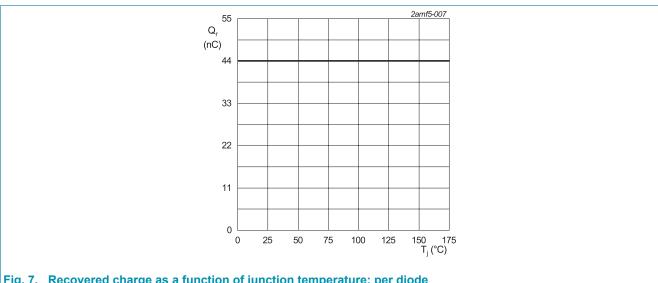
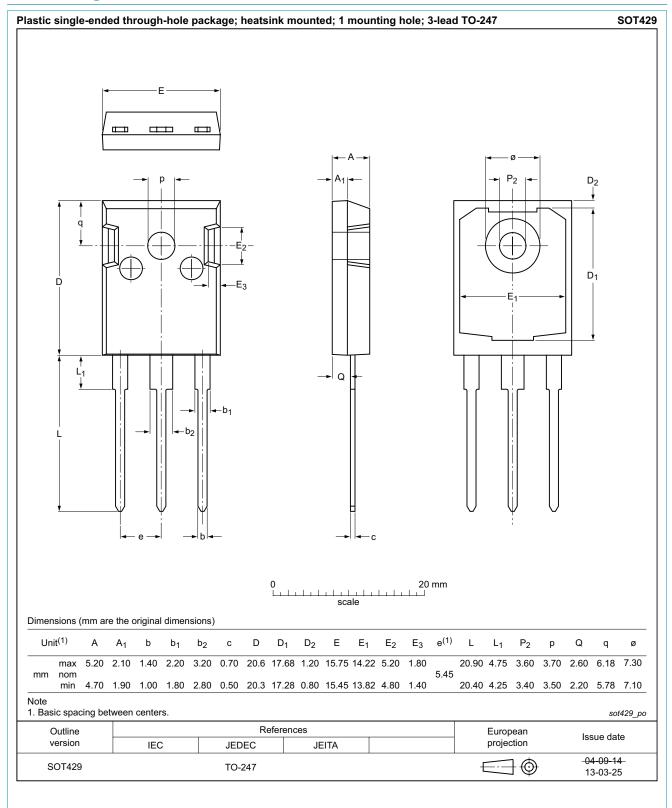


Fig. 7. Recovered charge as a function of junction temperature; per diode

# 11. Package outline



## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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